Shojan P Pavunny

List of Publications by Year
in descending order

50	837	516710 16	501196 28
papers	citations	h-index	g-index

50	50	50	1304
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Arrays of Si vacancies in 4H-SiC produced by focused Li ion beam implantation. Scientific Reports, 2021, 11, 3561.	3.3	16
2	Analyses of Substrate-Dependent Broadband Microwave (1â€“40 GHz) Dielectric Properties of Pulsed Laser Deposited Ba0.5Sr0.5TiO3 Films. Crystals, 2021, 11, 852.	2.2	1
3	Effect of La and Sc co-doping on dielectric and ferroelectric properties of PZT for energy storage capacitors. Journal of Applied Physics, 2021, 130, .	2.5	6
4	Freestanding n-Doped Graphene via Intercalation of Calcium and Magnesium into the Buffer Layerâ€“SiC(0001) Interface. Chemistry of Materials, 2020, 32, 6464-6482.	6.7	28
5	On the doping concentration dependence and dopant selectivity of photogenerated carrier assisted etching of 4Hâ€“SiC epilayers. Electrochimica Acta, 2019, 323, 134778.	5.2	3
6	A graphene integrated highly transparent resistive switching memory device. APL Materials, 2018, 6, .	5.1	26
7	Low-voltage-driven Pt/BiFeO3/DyScO3/p-Si-based metalâ€“ferroelectricâ€“insulatorâ€“semiconductor device for non-volatile memory. Journal of Materials Science, 2018, 53, 4274-4282.	3.7	5
8	Temperature dependent Raman scattering and electronic transitions in rare earth SmFeO3. Ceramics International, 2018, 44, 4198-4203.	4.8	30
9	Processing of Cavities in SiC Material for Quantum Technologies. Materials Science Forum, 2018, 924, 905-908.	0.3	3
10	Dielectric and Ferroelectric Properties of Rare Earth Doped Lead Zirconate Titanate Ceramics. ECS Meeting Abstracts, 2018, , .	0.0	0
11	Effect of Zr Substitution for Ti on BaZrxTi1â^'XO3 Thin Films for Energy Storage Applications. ECS Meeting Abstracts, 2018, , .	0.0	0
12	Photoelectrochemical Properties of p- and n- Type 4H-SiC Epilayers: Doping Concentration Dependence and Dopant Selectivity. ECS Meeting Abstracts, 2018, , .	0.0	0
13	Effect of off-center ion substitution in morphotropic lead zirconate titanate composition. Journal of Applied Physics, 2017, 121, 194102.	2.5	8
14	Ultrahigh capacitive energy storage in highly oriented Ba(ZrxTi1-x)O3 thin films prepared by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	3.3	51
15	Impact of Processing on Photoluminescence Properties of 4H-SiC for Potential Qubit Applications. ECS Meeting Abstracts, 2017, , .	0.0	0
16	Si:SrTiO3-Al2O3-Si:SrTiO3 multi-dielectric architecture for metal-insulator-metal capacitor applications. Applied Physics Letters, 2016, 109, 212901.	3.3	7
17	Nonpolar resistive memory switching with all four possible resistive switching modes in amorphous LaHoO3 thin films. Journal of Applied Physics, 2015, 118, .	2.5	18
18	Disorder driven structural and dielectric properties of silicon substituted strontium titanate. Journal of Applied Physics, 2015, 118, .	2.5	5

#	Article	IF	Citations
19	Unipolar resistive switching in planar Pt/BiFeO3/Pt structure. AIP Advances, 2015, 5, .	1.3	25
20	Holmium hafnate: An emerging electronic device material. Applied Physics Letters, 2015, 106, .	3.3	8
21	Optical properties and electronic band lineup on Si of amorphous zirconium modified Bi2Zn2/3Nb4/3O7 thin films. Journal of Alloys and Compounds, 2015, 644, 545-553.	5.5	6
22	The Thermalstability of Voltage Tunability in Pulsed Laser Deposited Ba_{0.6}Sr_{0.4}TiO₃Thin Films. Integrated Ferroelectrics, 2015, 166, 140-149.	0.7	5
23	Ferroelectric photovoltaic properties in doubly substituted (Bi0.9La0.1)(Fe0.97Ta0.03)O3 thin films. Applied Physics Letters, 2015, 106, .	3.3	35
24	Dielectric anomalies due to grain boundary conduction in chemically substituted BiFeO3. Journal of Applied Physics, 2015, 117, .	2.5	78
25	Unipolar resistive switching behavior of high-k ternary rare-earth oxide LaHoO3 thin films for non-volatile memory applications. Materials Research Society Symposia Proceedings, 2015, 1729, 23-28.	0.1	1
26	Structural phase transition of ternary dielectric SmGdO3: Evidence from angle dispersive x-ray diffraction and Raman spectroscopic studies. Journal of Applied Physics, 2015, 117, 094101.	2.5	9
27	Lanthanum Gadolinium Oxide: A New Electronic Device Material for CMOS Logic and Memory Devices. Materials, 2014, 7, 2669-2696.	2.9	15
28	Optical, ferroelectric, and piezoresponse force microscopy studies of pulsed laser deposited Aurivillius Bi5FeTi3O15 thin films. Journal of Applied Physics, 2014, 116, .	2.5	17
29	Multilevel unipolar resistive memory switching in amorphous SmGdO3 thin film. Applied Physics Letters, 2014, 104, 073501.	3.3	50
30	Properties of the new electronic device material LaGdO3(Phys. Status Solidi B 1/2014). Physica Status Solidi (B): Basic Research, 2014, 251, n/a-n/a.	1.5	0
31	Properties of the new electronic device material La<scp>G</scp>dO₃. Physica Status Solidi (B): Basic Research, 2014, 251, 131-139.	1.5	13
32	Resistive Switching and Current Conduction Mechanisms in Amorphous LaLuO₃ Thin Films Grown by Pulsed Laser Deposition. Integrated Ferroelectrics, 2014, 157, 47-56.	0.7	3
33	On the Resistive Switching and Current Conduction Mechanisms of Amorphous LaGdO₃Films Grown by Pulsed Laser Deposition. ECS Transactions, 2013, 53, 229-235.	0.5	10
34	Nonvolatile Resistive Memory Switching in Amorphous LaGdO3 Thin Films. Materials Research Society Symposia Proceedings, 2013, 1562, 1.	0.1	0
35	Analysis of Leakage Currents through PLD Grown Ultrathin a-LaGdO3 Based High-k Metal Gate Devices. Materials Research Society Symposia Proceedings, 2013, 1561, 1.	0.1	0
36	Advanced high-k dielectric amorphous LaGdO3 based high density metal-insulator-metal capacitors with sub-nanometer capacitance equivalent thickness. Applied Physics Letters, 2013, 102, .	3.3	12

#	Article	IF	Citations
37	Advanced high-k gate dielectric amorphous LaGdO3 gated metal-oxide-semiconductor devices with sub-nanometer equivalent oxide thickness. Applied Physics Letters, 2013, 102, .	3.3	13
38	Optical properties of amorphous high-k LaGdO3 films and its band alignment with Si. Journal of Applied Physics, 2012, 111, .	2.5	14
39	Cauchy-Urbach Dielectric Function Modeling of Amorphous High-k LaGdO3 Films. ECS Transactions, 2012, 45, 219-223.	0.5	4
40	Optical Dielectric Function Modeling and Electronic Band Lineup Estimation of Amorphous High-k LaGdO₃Films. ECS Journal of Solid State Science and Technology, 2012, 1, N53-N57.	1.8	6
41	Dielectric properties and electrical conduction of high-k LaGdO3ceramics. Journal of Applied Physics, 2012, 111, 102811.	2.5	20
42	Structural and Electrical Properties of Lanthanum Gadolinium Oxide: Ceramic and Thin Films for High-k Application. Integrated Ferroelectrics, 2011, 125, 44-52.	0.7	22
43	Fabrication and Electrical Characterization of High-k LaGdO₃ Thin Films and Field Effect Transistors. ECS Transactions, 2011, 35, 297-304.	0.5	4
44	Raman spectroscopy and field emission characterization of delafossite CuFeO2. Journal of Applied Physics, 2010, 107, .	2.5	89
45	Structural, electrical, and magnetic properties of chemical solution deposited BiFe1â^'xTixO3 and BiFe0.9Ti0.05Co0.05O3 thin films. Journal of Applied Physics, 2009, 106, 014103.	2.5	71
46	Temperature-Dependent Structural Disintegration of Delafossite CuFeO2. Materials Research Society Symposia Proceedings, 2009, 1183, 55.	0.1	1
47	Structural, electrical, and magnetic properties of chemical solution deposited Bi(Fe0.95Cr0.05)O3 thin films on platinized silicon substrates. Journal of Applied Physics, 2009, 105, .	2.5	35
48	Metalorganic chemical vapor deposited buffer layer in metalâ€“ferroelectricâ€“insulatorâ€“semiconductor diodes. Solid State Communications, 2009, 149, 2013-2016.	1.9	6
49	Preferential grain growth and improved fatigue endurance in Sr substituted PZT thin films on Pt(111)/TiOx/SiO2/Si substrates. Journal of Alloys and Compounds, 2009, 482, 253-255.	5.5	16
50	DyScO3 buffer layer for a performing metal-ferroelectric-insulator-semiconductor structure with multiferroic BiFeO3 thin film. Applied Physics Letters, 2009, 94, 142907.	3.3	42